

Title (en)
METHOD AND DEVICE FOR ETCHING A THIN CONDUCTIVE LAYER WHICH IS DISPOSED ON AN INSULATING PLATE SUCH AS TO FORM AN ELECTRODE NETWORK THEREON

Title (de)
VERFAHREN UND EINRICHTUNG ZUM ÄTZEN EINER DÜNNEN LEITFÄHIGEN SCHICHT, DIE AUF EINER ISOLIERENDEN PLATTE ANGEORDNET IST, UM DARAUF EIN ELEKTRODENNETZWERK ZU BILDEN

Title (fr)
PROCEDE ET DISPOSITIF POUR DECAPER UNE COUCHE MINCE CONDUCTRICE DEPOSEE SUR UNE PLAQUE ISOLANTE, DE MANIERE A Y FORMER UN RESEAU D'ELECTRODES.

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Application
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Priority
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Abstract (en)
[origin: WO03038852A1] The invention relates to a method and device for etching a thin conductive layer which is disposed on an insulating plate such as to form an electrode network thereon. Before the etching takes place, a protective film, comprising patterns corresponding to the electrodes in the network, is applied, said film being removed after etching. The inventive etching method consists in: moving the plate (1) in the general direction of the electrodes to be formed; circulating an electrochemical bath in a shear zone (7) which is defined by the surface of the layer to be etched and by the surface (61) of a counter electrode (10); and passing an electric current between the counter electrode (10) and the zones which are not protected by the protective film, said current being conveyed over a line of contacts which is disposed on the surface of the conductive layer (2) perpendicularly to the direction of passage D. In this way, etching homogeneity and network formation precision are improved.

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